

# PHOTOCOUPLER PS8701

# HIGH NOISE REDUCTION HIGH-SPEED ANALOG OUTPUT TYPE 5-PIN SOP PHOTOCOUPLER

#### **DESCRIPTION**

The PS8701 is an optically coupled isolator containing a GaAlAs LED on the light emitting diode (input side) and a PIN photodiode and a high-speed amplifier transistor on the output side on one chip.

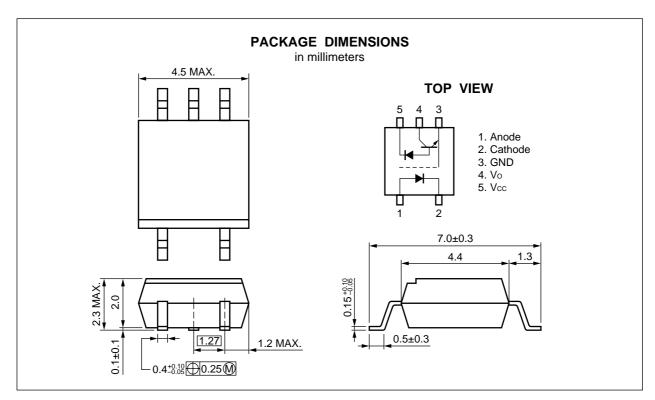
This is a plastic SOP (Small Out-line Package) type for high density applications.

#### **FEATURES**

- High common mode transient immunity (CMH, CML =  $\pm 10 \text{ kV/}\mu\text{s MIN.}$ )
- High supply voltage (Vcc = 35 V)
- High isolation voltage (BV = 2 500 Vr.m.s.)
- High-speed response (tphL = 0.8  $\mu$ s MAX., tpLH = 1.2  $\mu$ s MAX.)
- Taping product number (PS8701-E3, E4, F3, F4)

#### **APPLICATIONS**

- · Computer and peripheral manufactures
- General purpose inverter
- Substitutions for relays and pulse transformers
- · Power supply



The information in this document is subject to change without notice.



### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit	
Diode	Forward Current	lF	25	mA	
	Reverse Voltage	VR	3.0	V	
	Power Dissipation	Po	45	mW	
Detector	Supply Voltage	Vcc	35	V	
	Output Voltage	Vo	35	V	
	Output Current	lo	8.0	mA	
	Power Dissipation	Pc	100	mW	
Isolation Voltage <sup>1</sup>		BV	2 500	Vr.m.s.	
Operating Ambient Temperature		TA	-55 to +100	°C	
Storage Temperature		T <sub>stg</sub>	-55 to +125	°C	

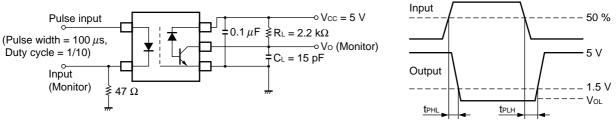
<sup>\*1</sup> AC voltage for 1 minute at T<sub>A</sub> = 25 °C, RH = 60 % between input and output

### ELECTRICAL CHARACTERISTICS (TA = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	VF	IF = 16 mA		1.7	2.2	V
	Reverse Current	lR	VR = 3 V			10	μΑ
	Forward Voltage Temperature Coefficient	$\Delta V_F/\Delta T$	I <sub>F</sub> = 16 mA		-1.6		mV/°C
	Terminal Capacitance	Ct	V = 0 V, f = 1 MHz		60		pF
Detector	High Level Output Current	Іон (1)	IF = 0 mA, Vcc = Vo = 5.5 V		3	500	nA
	High Level Output Current	Іон (2)	IF = 0 mA, Vcc = Vo = 30 V			100	μΑ
	Low Level Output Voltage	Vol	IF = 16 mA, Vcc = 4.5 V, Io = 1.2 mA		0.1	0.4	٧
	Low Level Supply Current	ICCL	IF = 16 mA, Vo = open, Vcc = 30 V		50		μΑ
	High Level Supply Current	Іссн	IF = 0 mA, Vo = open, Vcc = 30 V		0.01	2	
Coupled	Current Transfer Ratio	CTR	IF = 16 mA, Vcc = 4.5 V, Vo = 0.4 V	15	20	35	%
	Isolation Resistance	R <sub>I-O</sub>	V <sub>I-O</sub> = 1 kV <sub>DC</sub> , RH = 40 to 60 %	10 <sup>11</sup>			Ω
	Isolation Capacitance	C <sub>I-O</sub>	V = 0 V, f = 1 MHz		0.4		pF
	Propagation Delay Time (H → L) 11	tрнL	$I_F = 16 \text{ mA, } V_{CC} = 5 \text{ V, } R_L = 2.2 \text{ k}\Omega,$ $C_L = 15 \text{ pF}$		0.5	0.8	μs
	Propagation Delay Time (L → H) <sup>*1</sup>	tрLН			0.6	1.2	
	Common Mode Transient Immunity at High Level Output <sup>2</sup>	Смн	IF = 0 mA, Vcc = 5 V, RL = 4.1 k $\Omega$ , VcM = 1.5 kV	10			kV/μs
	Common Mode Transient Immunity at Low Level Output <sup>2</sup>	Смь	IF = 16 mA, Vcc = 5 V, RL = 4.1 k $\Omega$ , VcM = 1.5 kV	-10			

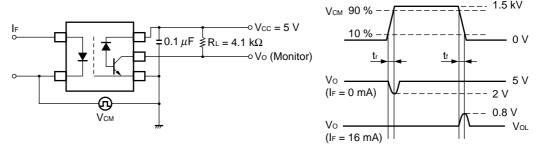


\*1 Test circuit for propagation delay time



C<sub>L</sub> is approximately 15 pF which includes probe and stray wiring capacitance

\*2 Test circuit for common mode transient immunity

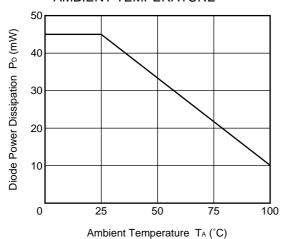


#### **USAGE CAUTIONS**

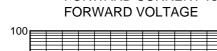
- 1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
- 2. By-pase capacitor of more than 0.1  $\mu F$  is used between Vcc and GND near device.

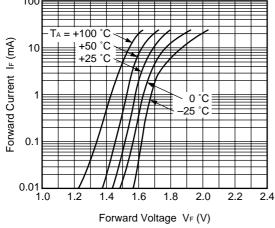
#### TYPICAL CHARACTERISTICS (TA = 25 °C, unless otherwise specified)

# DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE

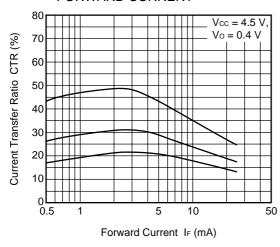


### FORWARD CURRENT vs.

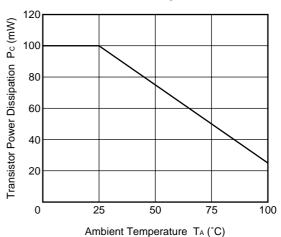




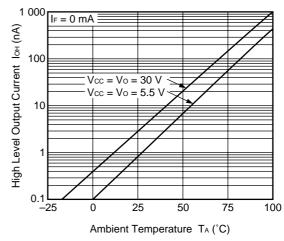
# CURRENT TRANSFER RATIO vs. FORWARD CURRENT



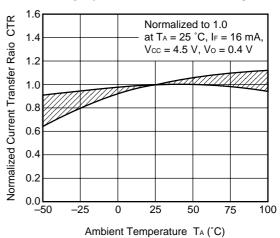
### TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



# HIGH LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE

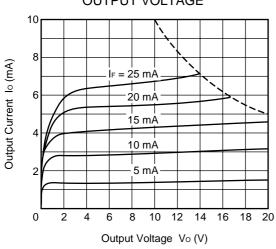


# NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE

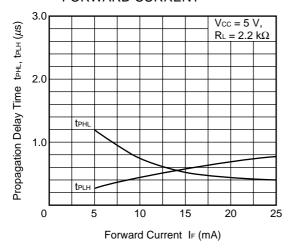


### **NEC**

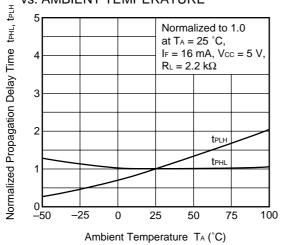
# OUTPUT CURRENT vs. OUTPUT VOLTAGE



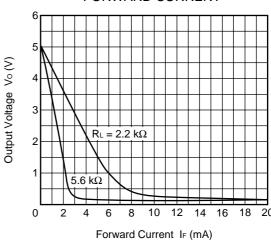
# PROPAGATION DELAY TIME vs. FORWARD CURRENT



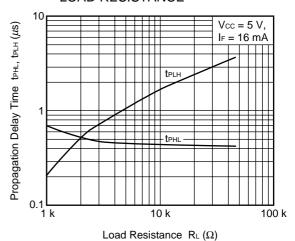
# NORMALIZED PROPAGATION DELAY TIME vs. AMBIENT TEMPERATURE



# OUTPUT VOLTAGE vs. FORWARD CURRENT

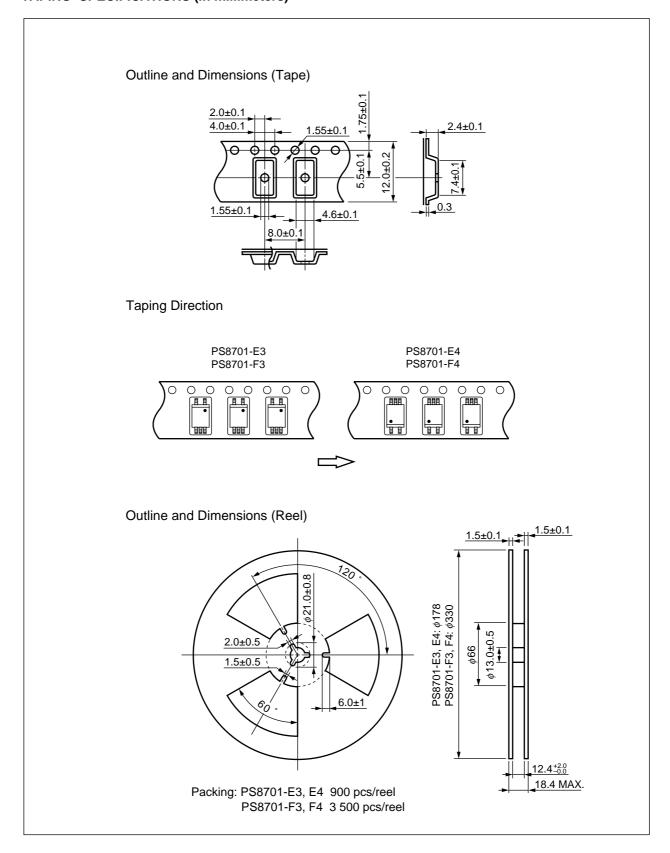


# PROPAGATION DELAY TIME vs. LOAD RESISTANCE





#### **TAPING SPECIFICATIONS (in millimeters)**





#### RECOMMENDED SOLDERING CONDITIONS

#### (1) Infrared reflow soldering

• Peak reflow temperature 235 °C (package surface temperature)

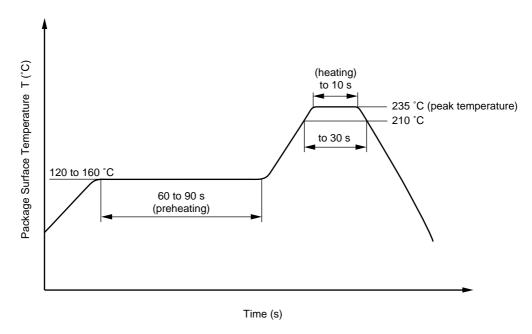
• Time of temperature higher than 210 °C 30 seconds or less

• Number of reflows Three

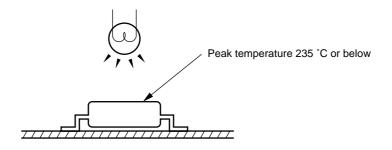
Flux
Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt % is recommended.)

#### Recommended Temperature Profile of Infrared Reflow



Caution Please avoid to removed the residual flux by water after the first reflow processes.



#### (2) Dip soldering

• Temperature 260 °C or below (molten solder temperature)

• Time 10 seconds or less

• Number of times One

• Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of

0.2 Wt % is recommended.)

#### **CAUTION**

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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Anti-radioactive design is not implemented in this product.

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